**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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| Applicant: | Yeo, *et al.* | Docket No.: | TSM03-0511 |
| Filed: | Herewith | Examiner: | TBD |
| Serial No.: | TBD | Art Unit: | TBD |
| For: | Multiple-Gate Transistors Formed on Bulk Substrates | | |

Mail Stop: Patent Application
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

## INFORMATION DISCLOSURE STATEMENT

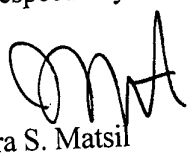
Dear Sir:

Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A that may be considered material to the examination of the above-identified application.

Pursuant to 37 CFR 1.98(a)(2)(i), as amended, copies of U.S. Patents cited are not being submitted. However, Applicant has included copies of the non-patent literature.

No fee is due at this time, as this Information Disclosure Statement is being filed concurrently with the patent application.

Respectfully submitted,



Ira S. Matsil
Attorney for Applicant
Reg. No. 35,272

September 24, 2003
Date

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
(972) 732-1001 (phone)
(972) 732-9218 (fax)

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Substitute for form 1449A/PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

Sheet 1 of 1

| Complete if Known | |
|---|---|
| Application Number | TBD |
| Filing Date | Herewith |
| First Named Inventor | Yeo, *et al.* |
| Art Unit | TBD |
| Examiner Name | TBD |
| Attorney Docket Number | TSM03-0511 |

**U.S. PATENT DOCUMENTS**

| Examiner Initials* | Cite No.[1] | Document Number: Number - Kind Code[2] (*if known*) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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| | | US- | | | |

**FOREIGN PATENT DOCUMENTS**

| Examiner Initials* | Cite No.[1] | Foreign Patent Document: Country Code[3] - Number[4] - Kind Code[5] (*if known*) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T[6] |
|---|---|---|---|---|---|---|
| | | | | | | |

**OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS**

| Examiner Initials* | Cite No.[1] | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, *magazine*, *journal*, *serial*, *symposium*, *catalog*, *etc.*), date, *page(s)*, *volume-issue* number(s), publisher, city and/or country where published. | T[2] |
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| | K | CHAU, R., *et al.* "Advanced Depleted-Substrate Transistors: Single-gate, Double-gate and Tri-gate," Extended Abstracts of the 2002 International Conference on Solid State Devices and Materials, (2002) pp. 68-69. | |
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| Examiner Signature | | Date Considered | |
|---|---|---|---|

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. [1]Applicant's unique citation designation number (optional). [2]See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3]Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4]For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5]Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6]Applicant is to place a check mark here if English language Translation is attached.